# ATENT COOPERATION TREALY

From the INTERNATIONAL SEARCHING AUTHORITY

SEMICONDUCTOR ENERGY LABORATORY CO., LTD.

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# PCT

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43 bis.1)

Date of mailing 27.12.2005 (day/month/year) Applicant's or agent's file reference FOR FURTHER ACTION See paragraph 2 below International application No. International filing date (day/month/year) Priority date (day/month/year) PCT/JP2005/017223 13.09.2005 15.09.2004 International Patent Classification (IPC) or both national classification and IPC

Int.Cl. H01L29/786 (2006.01), H01L21/336 (2006.01), G02F1/1368 (2006.01)

Applicant

00000PCT8160

SEMICONDUCTOR ENERGY LABORATORY CO. T.TD

	District Billion Billion Co., Hib.							
1.	This	This opinion contains indications relating to the following items:						
	Y	Box No. I	Basis of the opinion					
		Вох №. П	Priority					
		Box No. III	Non-establishment of opinion with regard to novelty, inventive step and industrial applicability					
		Box No. IV	Lack of unity of invention					
	☑.	Box No. V	Reasoned statement under Rule 43 bis.1(a)(i) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement					
		Box No. VI	Certain documents cited					
		Box No. VII	Certain defects in the international application					
		Вох №. VШ	Certain observations on the international application					
2.	FURTHER ACTION  If a demand for international preliminary examination is made, this opinion will be considered to be a written opinion of International Preliminary Examining Authority ("IPEA") except that this does not apply where the applicant chooses an Authority than this one to be the IPEA and the chosen IPEA has notified the International Bureau under Rule 66.1bis(b) that wropinions of this International Searching Authority will not be so considered.							
	a writ	If this opinion is, as provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA a written reply together, where appropriate, with amendments, before the expiration of 3 months from the date of mailing of Form PCT/ISA/220 or before the expiration of 22 months from the priority date, whichever expires later.						
	For further options, see Form PCT/ISA/220.							
3.	For further details, see notes to Form PCT/ISA/220.							

Date of completion of this opinion 2	5.11.2005		
Name and mailing address of the ISA/JP	Authorized officer	4M	9449
Japan Patent Office	Shigemasa MATSUDA		
3-4-3, Kasumigaseki, Chiyoda-ku, Tokyo 100-891		3462	

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# WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2005/017223

Вс	x No. I	Basis of the opinion					
1	With	regard to the learnings this colinian has been contributed and but in f					
1.	regard to the language, this opinion has been established on the basis of: the international application in the language in which it was filed						
	1	a translation of the international application into , which is the language of a translation furnished for the purposes of international search (Rules 12.3(a) and 23.1(b)).					
		The second section and purposes of international search (Nules 12.5(a) and 25.1(b)).					
2.	With regard to any nuclectide and/or amino acid sequence disclosed in the international application and necessary to claimed invention, this opinion has been established on the basis of:						
	a. type	of material					
		a sequence listing					
		table(s) related to the sequence listing					
		,					
	b. form	nat of material					
		on paper					
		in electronic form					
		of filing/furnishing					
		contained in the international application as filed					
		filed together with the international application in electronic form					
		furnished subsequently to this Authority for the purposes of search					
3.	í	in addition, in the case that more than one version or copy of a sequence listing and/or table(s) relating thereto has been iled or furnished, the required statements that the information in the subsequent or additional copies is identical to that in the application as filed or does not go beyond the application as filed, as appropriate, were furnished.					
4.	Additio	nal comments:					
••	, iodii, o	ina comments.					
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# WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

Claims

Claims

Inte. .. ational application No.

PCT/JP2005/017223

YES

NO

	nuve step or industrial applicability;			
1.	Statement			·
	Novelty (N)	Claims Claims	1-14	YES NO
	Inventive step (IS)	Claims Claims	1-14	YES NO

## 2. Citations and explanations:

Industrial applicability (IA)

D1:JP 2001-281694 A (SEMICONDUCTOR ENERGY LABORATORY CO., Ltd.) 2001.10.10, Figs.4,6,17,18 (Family: None)

1 - 14

D2:JP 6-202146 A(FUJITSU, Ltd.)1994.07.22, Whole Document (Family: None)

D3:JP 2001-281704 A (SEMICONDUCTOR ENERGY LABORATORY CO., Ltd.)

2001.10.10, Fig.16 & US 2002/0110941 A1

D4:JP 7-312425 A (HITACHI, Ltd.) 1995.11.28, Fig.3(Family: None)

### Claims1, 2, 5-14

In the cited document D1,

A semiconductor device, which is a mobile information terminal etc., comprising TFTs having an electrode by stacking a first conductive layer (Ti) in contact with the semiconductor thin film and a second conductive layer (Al) on the first conductive layer. And, the first conductive layer has a portion projected from an end portion of the second conductive layer, wherein ITO, which is for the light-emitting element or the liquid crystal element, is in contact with the portion of the first conductive film. In the cited document D2,

An electrode, such an art, has a tapered portion in order to securely connect.

Therefore, it is perceived that a person skilled in the art could have easily made the invention by applying the technique of cited document D2 to the semiconductor device of cited document D1.

### Claim3,4

In the cited document D3,

A multilayer electrode, wherein a side surface portion of a first conductive layer has a smaller tapered angle than that of a second conductive layer. In the cited document D4,

A multilayer electrode, wherein a side surface portion of a first conductive layer has a larger tapered angle than that of a second conductive layer. Therefore, it is perceived that a person skilled in the art could have easily made the invention by applying the techniques of cited documents D2-4 to the semiconductor device of cited document D1.